N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]
60	0.0018 at V_{GS} = 10 V	180
	0.0028 at V_{GS} = 4.5 V	155

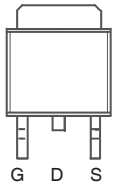
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested

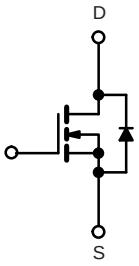
Pb-free

RoHS COMPLIANT

TO-252



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current (T_J = 175 °C)[b]	T_C = 25 °C	I_D	180	A
	T_C = 100 °C		135[a]	
Pulsed Drain Current		I_{DM}	720	
Continuous Source Current (Diode Conduction)		I_S	180[a]	
Avalanche Current		I_{AS}	150	
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E_{AS}	330	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	255	W
	T_A = 25 °C		6.9[b]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	8	15	°C/W
	Steady State		12	45	
Maximum Junction-to-Case		R_{thJC}	0.9	1.5	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t ≤ 10 s.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.[a]**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1	-	3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 48 V, V_{GS} = 0 V			1	µA
		V_{DS} = 48 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 48 V, V_{GS} = 0 V, T_J = 175 °C			250	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	180			A
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		0.0018	0.0026	Ω
		V_{GS} = 10 V, I_D =20 A, T_J = 125 °C		0.0023	0.0032	
		V_{GS} = 10 V, I_D =15 A, T_J = 175 °C		0.0029	0.0042	
		V_{GS} = 4.5 V, I_D = 15 A		0.0028	0.0039	
Forward Transconductance[b]	g_{fs}	V_{DS} = 48 V, I_D = 20 A		175		S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 48 V, f = 1 MHz		11050		pF
Output Capacitance	C_{oss}			1650		
Reverse Transfer Capacitance	C_{rss}			185		
Total Gate Charge[c]	Q_g	V_{DS} = 48 V, V_{GS} = 10 V, I_D = 20 A		79		nC
Gate-Source Charge[c]	Q_{gs}			16		
Gate-Drain Charge[c]	Q_{gd}			20		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 48 V, R_L = 0.6 Ω I_D ≅ 20 A, V_{GEN} = 10 V, R_g = 2.5 Ω		20		ns
Rise Time[c]	t_r			35		
Turn-Off Delay Time[c]	$t_{d(off)}$			68		
Fall Time[c]	t_f			15		
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)						
Pulsed Current	I_{SM}				720	A
Diode Forward Voltage	V_{SD}	I_F = 20 A, V_{GS} = 0 V			1.25	V
Reverse Recovery Time	t_{rr}	I_F = 20 A, di/dt = 100 A/µs		73		ns

Notes:

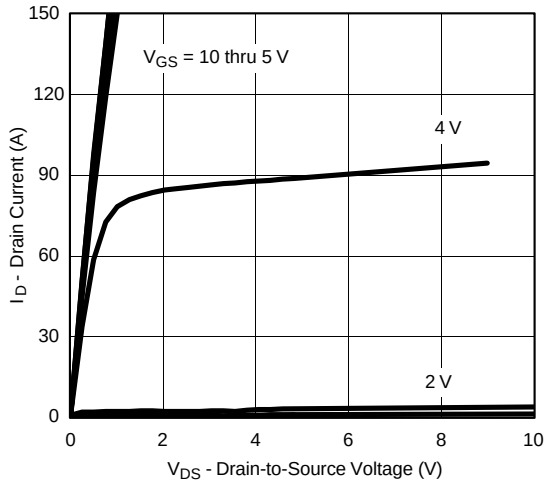
a. For design aid only; not subject to production testing.

b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

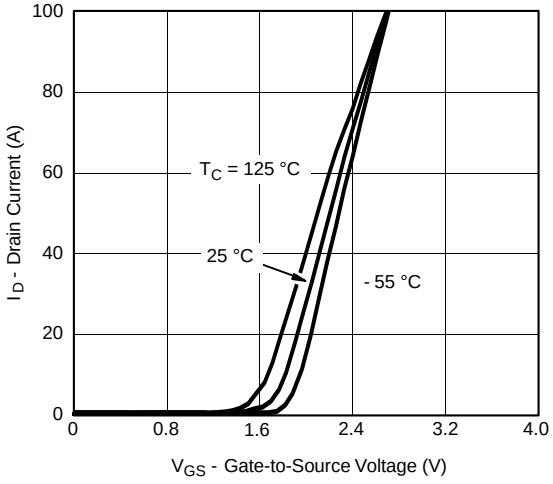
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

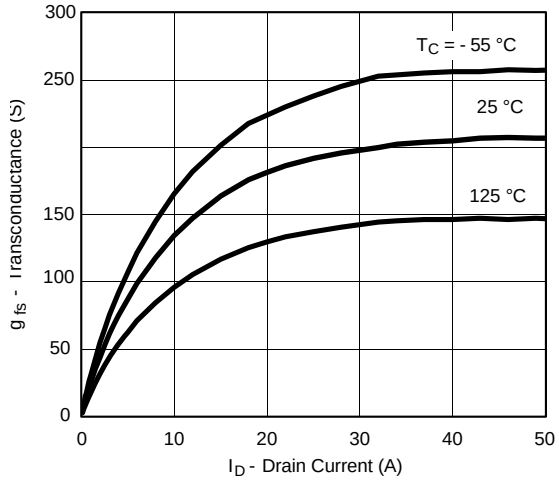
TYPICAL CHARACTERISTICS (25 °C unless noted)



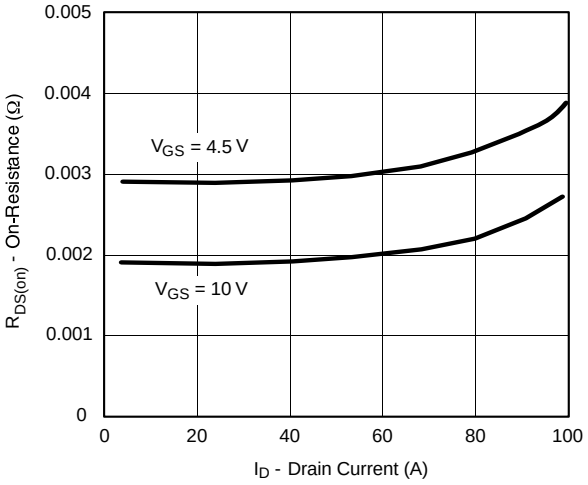
Output Characteristics



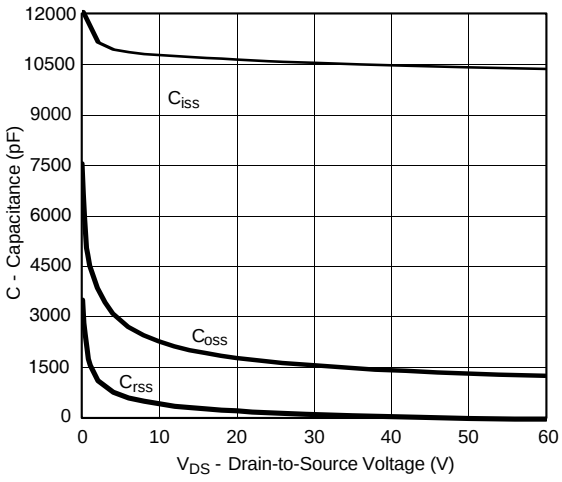
Transfer Characteristics



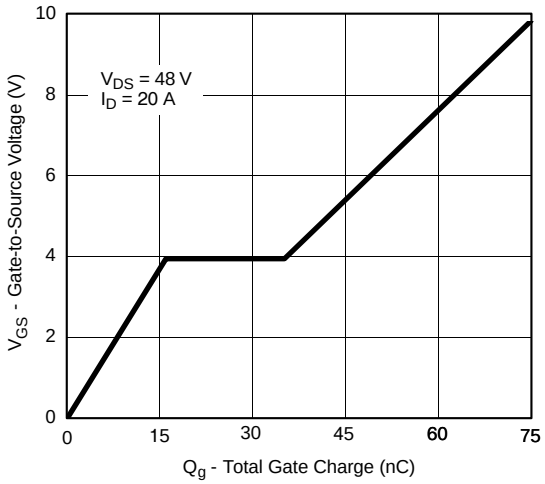
Transconductance



On-Resistance vs. Drain Current

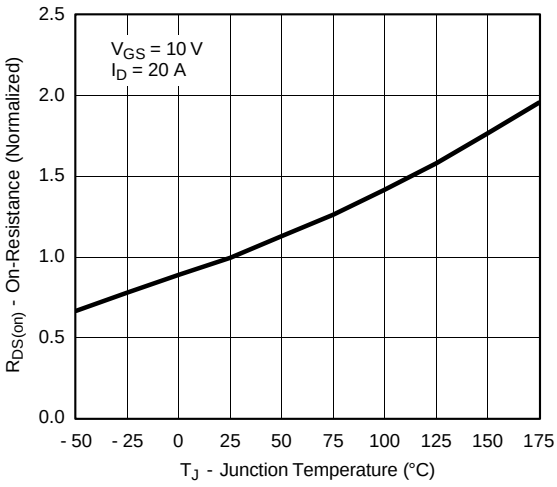


Capacitance

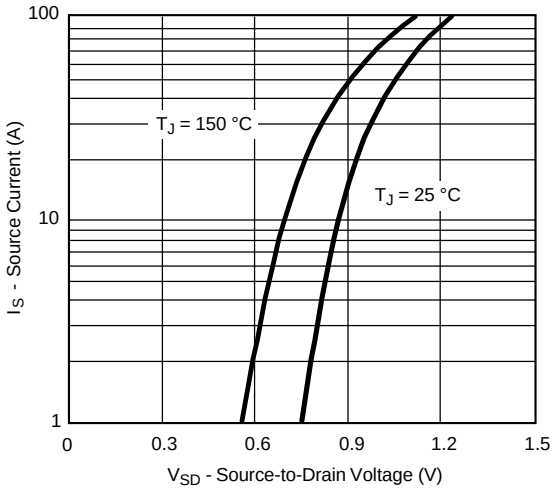


Gate Charge

TYPICAL CHARACTERISTICS (25 °C unless noted)

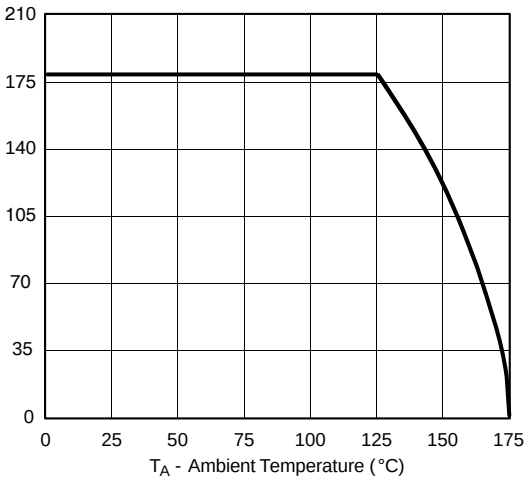


On-Resistance vs. Junction Temperature

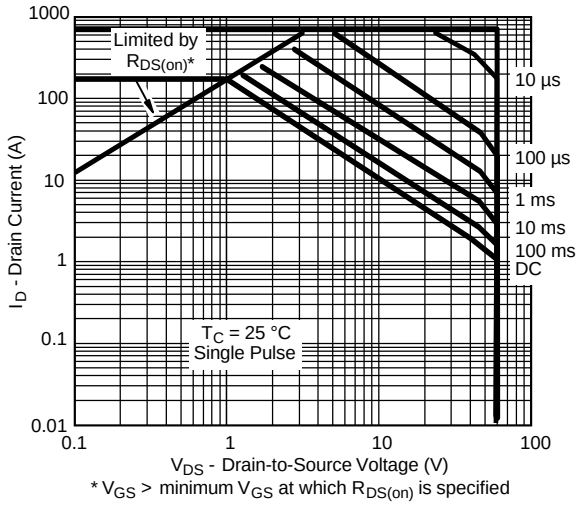


Source-Drain Diode Forward Voltage

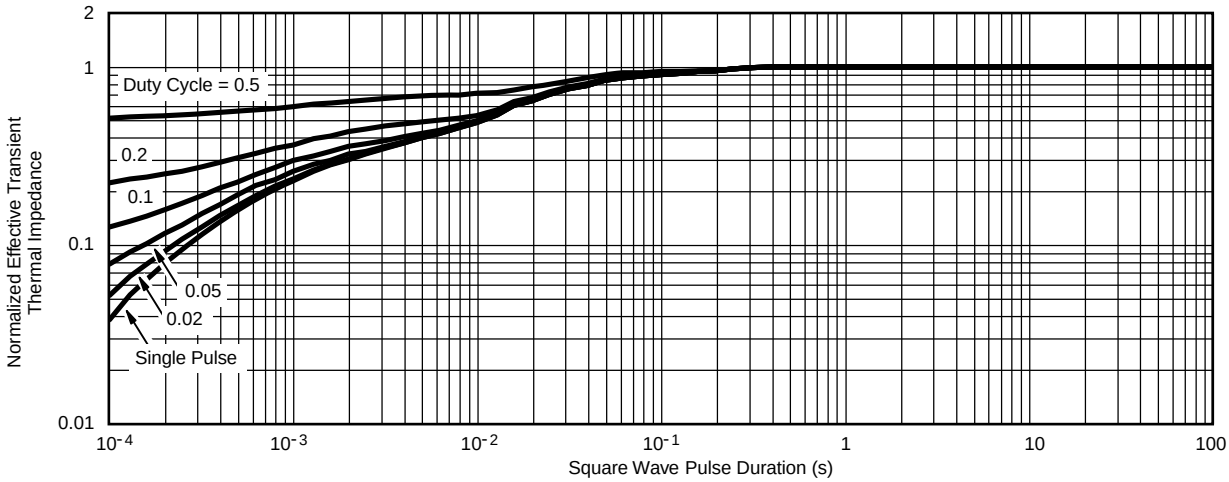
THERMAL RATINGS



Maximum Drain Current vs. Ambient Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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